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CLEANING METHOD FOR SEMICONDUCTOR

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ABSTRACT

PURPOSE: To clean a semiconductor wafer in a state that an impurity is not contained without necessity of a large ultrapure water generating facility by utilizing water generated by the reaction of high purity hydrogen gas and oxygen gas for cleaning the wafer.

CONSTITUTION: High purity oxygen gas and hydrogen gas are made to flow from gas inlets to quartz tubes 2, 3, while hydrogen gas is burnt by the operation of an ignition heater 9 mounted at a part of the tube 3 to generate water. An ammeter or a voltmeter 10 is added to the heater to regulate the temperature, a semiconductor wafer 7 is cleaned by the generated water or steam, and excess water or steam is exhausted from an outlet 11. Since the cleaning is conducted with steam state water, it is dried naturally, but a heat source 8 is mounted in a supporting base 6 for the purpose of raising the efficiency of cleaning and drying.

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